

What is claimed is:

1. A semiconductor device comprising:
 - a substrate;
 - 5 a seal layer which seals a semiconductor element formed on the substrate, wherein a side surface of the seal layer is positioned inside of a side surface of the substrate.
- 10 2. The semiconductor device according to claim 1, wherein the side surface of the seal layer has a cut cross-section formed by grinding, and the side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.
- 15 3. The semiconductor device according to claim 1, wherein the side surface of the seal layer is positioned inside of the side surface of the substrate within a range of 5μm to 100μm.
- 20 4. The semiconductor device according to claim 1, wherein the substrate is a silicon substrate or a sapphire substrate whose surface is formed with a silicon thin film.
- 25 5. A semiconductor device comprising:
 - a substrate;
 - a sealing resin sealing a semiconductor element formed on the substrate, wherein a side surface of the sealing resin is positioned inside of a side surface of the substrate.
6. The semiconductor device according to claim 5, wherein the side surface

of the sealing resin has a cut cross-section formed by grinding, and the side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.

7. The semiconductor device according to claim 5, wherein the side surface
5 of the sealing resin is positioned inside of the side surface of the substrate within a range of 5μm to 100μm.

8. The semiconductor device according to claim 5, wherein the substrate is a silicon substrate or a sapphire substrate whose surface is formed with a silicon thin
10 film.

9. A semiconductor device comprising:
a substrate which has a main surface formed with a circuit element;
a wiring which is formed over the main surface and which is electrically
15 connected to the circuit element;
a sealing resin which covers the main surface of the substrate and the
wiring; and

an external terminal which is electrically connected to the wiring and which is exposed from a surface of the sealing resin,

20 wherein an edge of the sealing resin is formed inside an edge of the substrate.

10. The semiconductor device according to claim 9, wherein a side surface of the sealing resin has a cut cross-section formed by grinding, and a side surface of the
25 substrate has a cut cross-section formed by applying laser light to the substrate.

11. The semiconductor device according to claim 9, wherein the side surface

of the sealing resin is positioned inside of a side surface of the substrate within a range of 5 μ m to 100 μ m.

12. The semiconductor device according to claim 9, wherein the substrate is

5 a silicon substrate or a sapphire substrate whose surface is formed with a silicon thin film.

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